IN THE CLAIMS

Please amend claims 1, 15, 21 and 22 as follows:

Claim 1 (Currently Amended): An electrode structure including a bonding pad formed on an insulation film without penetrating the insulation film, the insulation film being formed above a base structure,

the insulation film comprising a plurality of poles of polyimide, a first film formed on each side surfaces of the poles and formed of an insulation material having a higher hardness than polyimide, and a second film of polyimide buried among said a plurality of poles with the first film formed on the side surface thereof,

wherein said plurality of poles are surrounded with the first film respectively.

Claim 2 (Canceled).

Claim 3 (Previously Presented): A semiconductor light-emitting device having a waveguide including an active layer or a light absorption layer, a lower electrode formed below the waveguide, and an upper electrode formed above the waveguide,

the upper electrode having an electrode structure,

the electrode structure including a bonding pad formed on an insulation film without penetrating the insulation film, the insulation film being formed above a base substrate,

the insulation film comprising a plurality of poles of polyimide, a first film formed on each

side surfaces of the poles and formed of an insulation material having a higher hardness than polyimide, and a second film of polyimide buried among said a plurality of poles with the first film formed on side surfaces thereof.

Claim 4 (Original): A semiconductor light-emitting device according to claim 3, wherein the first film is also formed on upper surfaces of the poles.

Claim 5 (Canceled).

Claim 6 (Previously Presented): A semiconductor light-emitting device according to claim 3, wherein

the first film is also formed on upper surfaces of the second film.

Claim 7 (Previously Presented): A semiconductor light-emitting device according to claim 3, wherein

a third film of an insulation material is sandwiched between the insulation film and the bonding pad.

Claims 8-10 (Canceled).

Claim 11 (Previously Presented): A semiconductor light-emitting device according to claim 3, wherein

the insulation film is formed on a layer formed on the base substrate, the layer being formed of a material having a higher hardness than the polyamide.

Claims 12-14 (Canceled).

Claim 15 (Currently Amended): A semiconductor light-emitting device according to claim ~~13~~ 3, further comprising

a high resistance layer formed on a side of the waveguide; and

said electrode structure formed on the high resistance layer.

Claims 16-18 (Canceled).

Claim 19 (Previously Presented): An electrode structure according to claim 1, wherein the first film is also formed on upper surfaces of the second film.

Claim 20 (Previously Presented): A semiconductor light-emitting device according to claim 1, wherein the first film is also formed on upper surfaces of the second film.

Claim 21 (Currently Amended): A semiconductor light-emitting device according to claim ~~13~~ 3, wherein

the first film is also formed on upper surfaces of the poles.

Claim 22 (Currently Amended): A semiconductor light-emitting device according to claim ~~13~~ 3, wherein

the first film is also formed on upper surfaces of the second film.